Thyristor Module

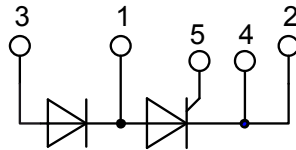|			
V_{RRM}	= 2x	800	V
I_{TAV}	=	49	A
V_T	=	1.34	V

Phase leg

Part number

MCD44-08io1B
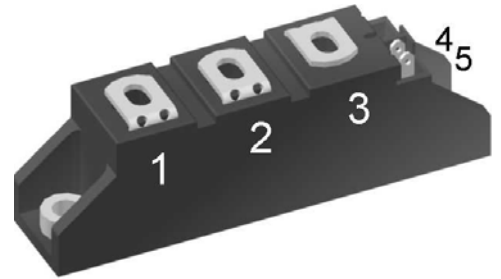
Backside: isolated

E72873

Features / Advantages:

● Thyristor for line frequency
● Planar passivated chip
● Long-term stability
● Direct Copper Bonded Al2O3-ceramic

Applications:

● Line rectifying 50/60 Hz
● Softstart AC motor control
● DC Motor control
● Power converter
● AC power control
● Lighting and temperature control

Package: TO-240AA

● Isolation Voltage: 3600 V~
● Industry standard outline
● RoHS compliant
● Soldering pins for PCB mounting
● Base plate: DCB ceramic
● Reduced weight
● Advanced power cycling

Rectifier | | | | Ratings | | |

Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	T_{VJ} = 25°C				900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	T_{VJ} = 25°C				800	V
$I_{R/D}$	reverse current, drain current	$V_{R/D}$ = 800 V	T_{VJ} = 25°C			100	µA
		$V_{R/D}$ = 800 V	T_{VJ} = 125°C			5	mA
V_T	forward voltage drop	I_T = 100 A	T_{VJ} = 25°C			1.34	V
		I_T = 200 A				1.75	V
		I_T = 100 A	T_{VJ} = 125°C			1.34	V
		I_T = 200 A				1.80	V
I_{TAV}	average forward current	T_C = 85°C	T_{VJ} = 125°C			49	A
$I_{T(RMS)}$	RMS forward current	180° sine				77	A
V_{T0}	threshold voltage } for power loss calculation only		T_{VJ} = 125°C			0.85	V
r_T	slope resistance					5.3	mΩ
R_{thJC}	thermal resistance junction to case					0.53	K/W
R_{thCH}	thermal resistance case to heatsink				0.20		K/W
P_{tot}	total power dissipation	T_C = 25°C				180	W
I_{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			1.15	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.24	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 125°C			980	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.06	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			6.62	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			6.40	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 125°C			4.80	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			4.63	kA²s
C_J	junction capacitance	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		54		pF
P_{GM}	max. gate power dissipation	t_P = 30 µs	T_C = 125°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	T_{VJ} = 125°C; f = 50 Hz repetitive, I_T = 150 A				150	A/µs
		t_P = 200 µs; di_G/dt = 0.45 A/µs;					
		I_G = 0.45A; V_D = ⅔ V_{DRM} non-repet., I_T = 49 A				500	A/µs
$(dv/dt)_{cr}$	critical rate of rise of voltage	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			1000	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	V_D = 6 V	T_{VJ} = 25°C			1.5	V
			T_{VJ} = -40°C			1.6	V
I_{GT}	gate trigger current	V_D = 6 V	T_{VJ} = 25°C			100	mA
			T_{VJ} = -40°C			200	mA
V_{GD}	gate non-trigger voltage	V_D = ⅔ V_{DRM}	T_{VJ} = 125°C			0.2	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	t_p = 10 µs	T_{VJ} = 25°C			450	mA
		I_G = 0.45A; di_G/dt = 0.45 A/µs					
I_H	holding current	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			200	mA
t_{gd}	gate controlled delay time	V_D = ½ V_{DRM}	T_{VJ} = 25°C			2	µs
		I_G = 0.45A; di_G/dt = 0.45 A/µs					
t_q	turn-off time	V_R = 100 V; I_T = 120 A; V_D = ⅔ V_{DRM} T_{VJ} = 125°C			150		µs
		di/dt = 10 A/µs; dv/dt = 20 V/µs; t_p = 200 µs					

Package	TO-240AA			Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				200	A
T_{VJ}	virtual junction temperature			-40		125	°C
T_{op}	operation temperature			-40		100	°C
T_{stg}	storage temperature			-40		125	°C
Weight					90		g
M_D	mounting torque			2.5		4	Nm
M_T	terminal torque			2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface | striking distance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600			V
		t = 1 minute		3000			V

IXYS ⒩
Type name
YYWWx
Circuit Diagram
Date Code
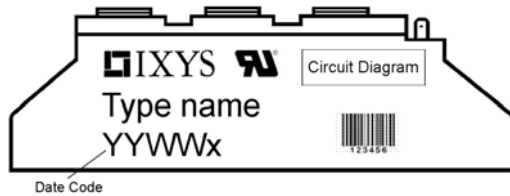
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD44-08io1B	MCD44-08io1B	Box	0	

Similar Part	Package	Voltage class
MCMA50PD1200TB	TO-240AA-1B	1200
MCMA65PD1200TB	TO-240AA-1B	1200

Equivalent Circuits for Simulation   *on die level* T_{VJ} = 125 °C
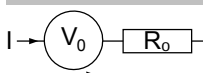
Thyristor

$V_{0\,max}$	threshold voltage	0.85	V
$R_{0\,max}$	slope resistance *	4.1	mΩ

Outlines   TO-240AA

A 2.8 - 0.8
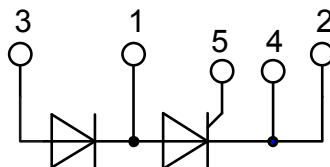DIN 46244
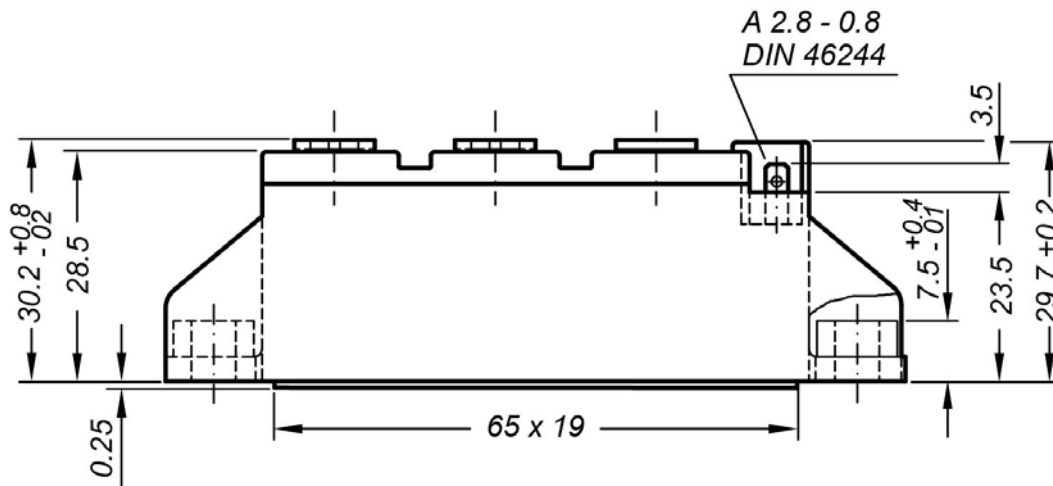
General tolerance: DIN ISO 2768 class „c"

M5
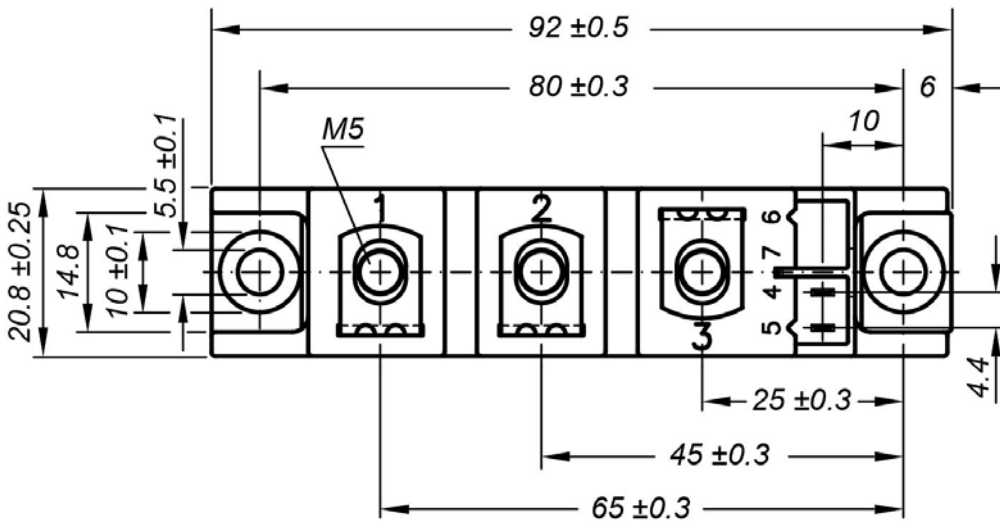
Optional accessories: Keyed gate/cathode twin plugs
Wire length: 350 mm, gate = white, cathode = red
UL 758, style 3751
Type **ZY 200L**   (L = Left   for pin pair 4/5)

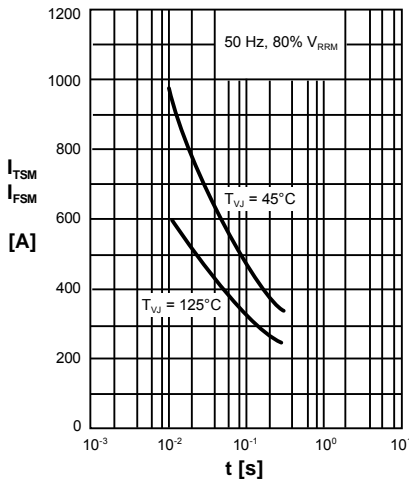Data according to IEC 60747and per semiconductor unless otherwise specified   20130605a

![IXYS logo]

Thyristor

Fig. 1 Surge overload current
I_{TSM}, I_{FSM}: Crest value, t: duration
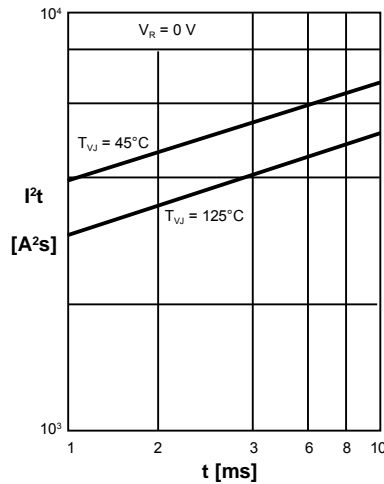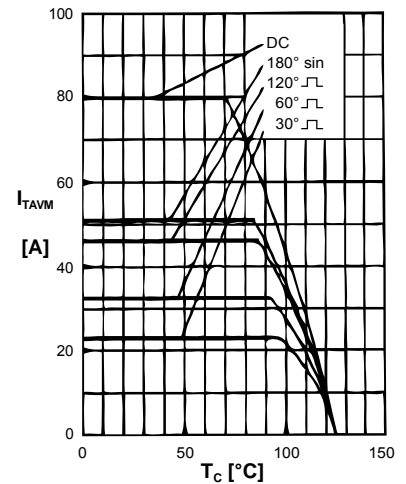

Fig. 2 I²t versus time (1-10 ms)

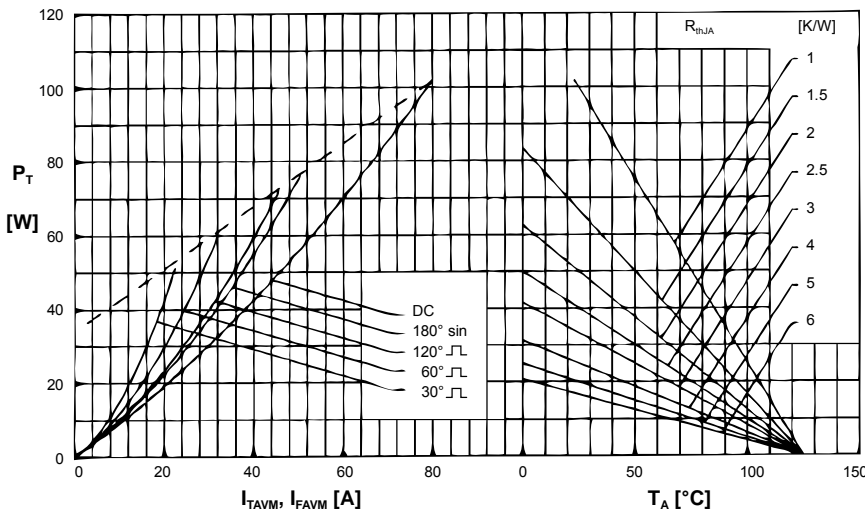Fig. 3 Maximum forward current at case temperature

Fig. 4 Power dissipation vs. onstate current and ambient temperature (per thyristor/diode)
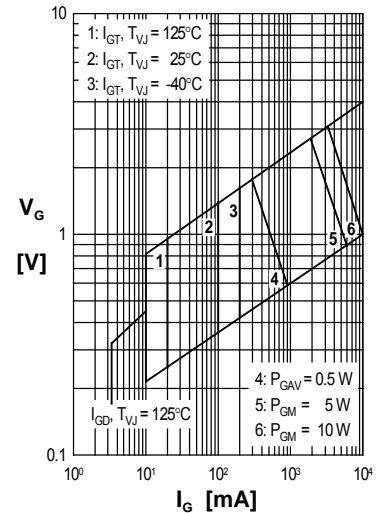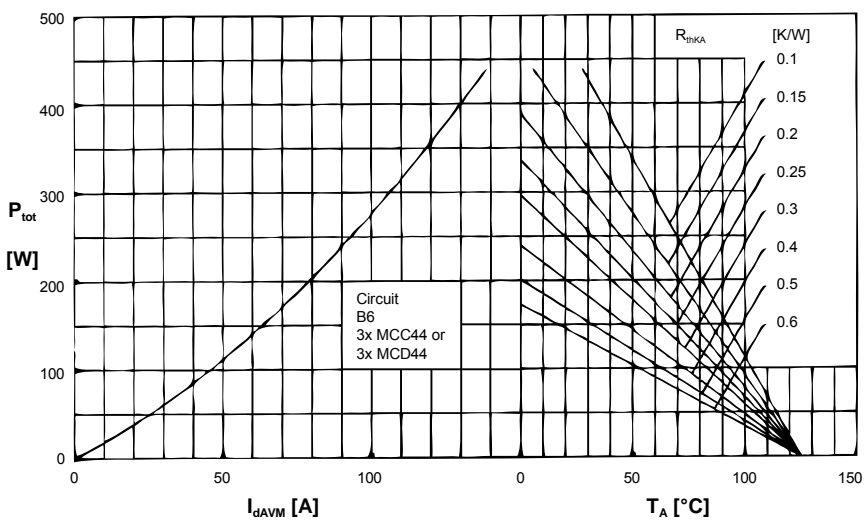

Fig. 5 Gate trigger characteristics

Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature
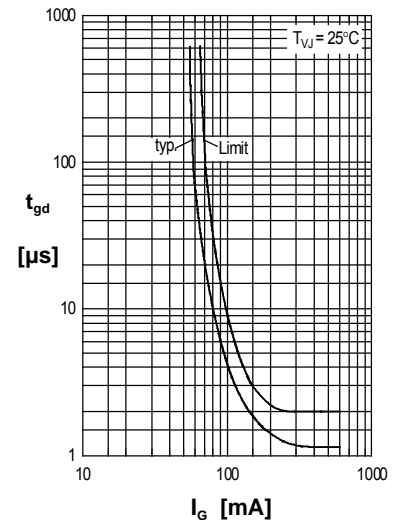

Fig. 7 Gate trigger delay time

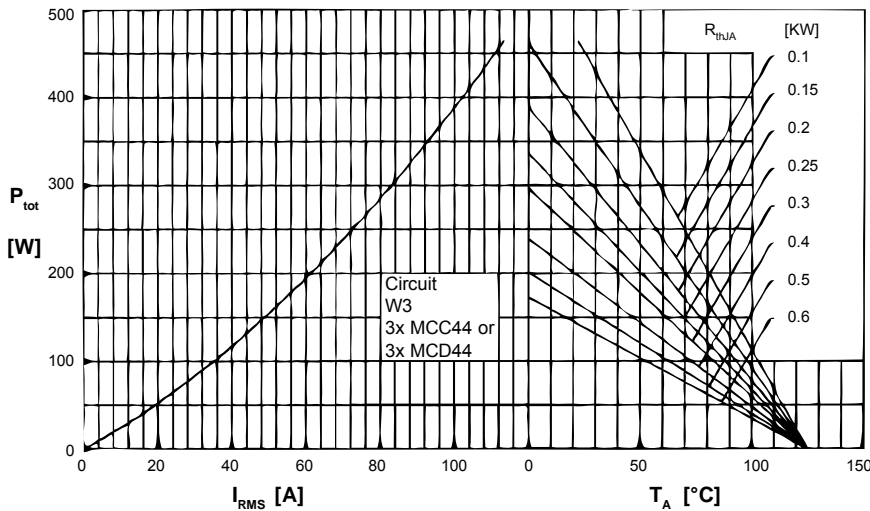
IXYS reserves the right to change limits, conditions and dimensions.

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Rectifier

Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

R_{thJA} [KW]
0.1
0.15
0.2
0.25
0.3
0.4
0.5
0.6

Circuit W3
3x MCC44 or
3x MCD44

P_{tot} [W]

I_{RMS} [A]

T_A [°C]
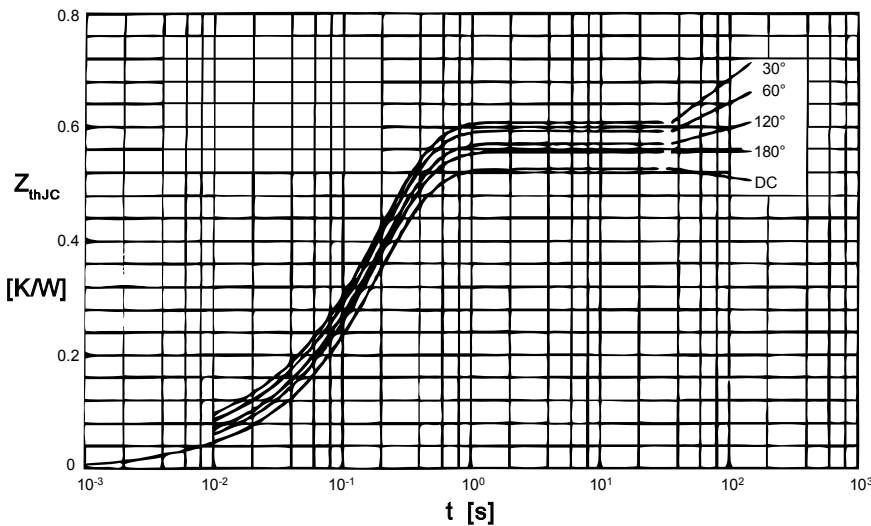
Fig. 9 Transient thermal impedance junction to case (per thyristor)

Z_{thJC} [K/W]

t [s]

30°
60°
120°
180°
DC

R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.53
180°	0.55
120°	0.58
60°	0.60
30°	0.62

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.015	0.0035
2	0.026	0.0200
3	0.489	0.1950
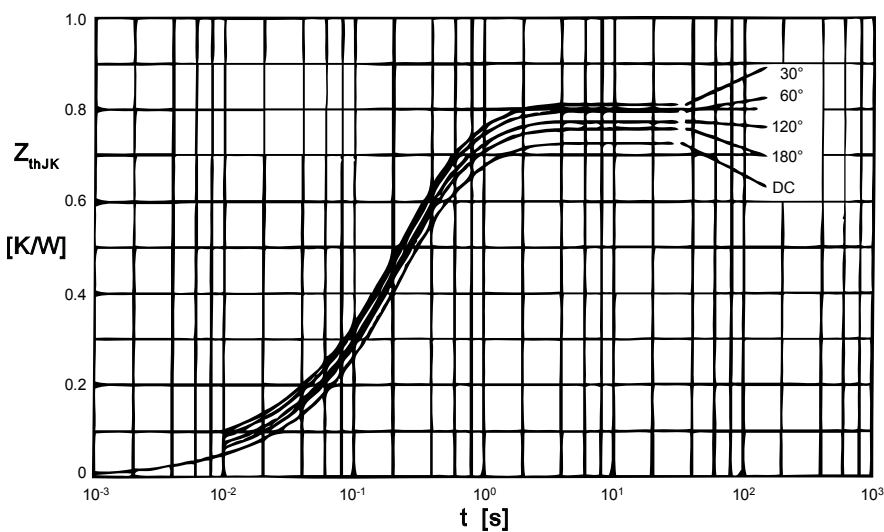
Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

Z_{thJK} [K/W]

t [s]

30°
60°
120°
180°
DC

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.73
180°	0.75
120°	0.78
60°	0.80
30°	0.82

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.015	0.0035
2	0.026	0.0200
3	0.489	0.0195
4	0.200	0.6800

Data according to IEC 60747and per semiconductor unless otherwise specified

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